

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (currently amended) A pattern forming method ~~which is characterized in~~ comprising the steps of:

[1] ~~a step of~~ applying on a substrate material a photosensitive composition comprising (a) an alkali-soluble resin, (b) a photosensitizer having a quinone diazide group, (c) a photo acid generator, (d) a crosslinking agent and (e) a solvent to form a photosensitive layer[.];

[2] ~~a step of~~ exposing the photosensitive layer in light through a mask[.];

[3] ~~a step of~~ removing said exposed area by development to form a positive image[.];
and ~~then~~

[4] ~~a step of~~ exposing a whole area of the positive image to light.

2. (currently amended) The pattern forming method ~~which is characterized in that in the pattern forming method~~ according to claim 1[.] wherein (b) [[a]] the photosensitizer having a quinone diazide group and (c) [[a]] the photo acid generator have an absorption activity at the same exposure wavelength and the whole area exposure is conducted at the exposure wavelength where both the photosensitizer and the ~~photo acid~~ photo acid generator have an absorption activity.

3. (currently amended) A pattern forming method ~~which is characterized in~~ comprising the steps of:

[1] ~~a step of~~ applying on a substrate material a photosensitive composition comprising (a) an alkali-soluble resin, (f) a compound having a quinone diazide group and functioning as

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a photosensitizer and a ~~photo-acid~~ photo acid generator, (d) a crosslinking agent and (e) a solvent to form a photosensitive layer[.];

[2] ~~a step of~~ exposing the photosensitive layer in light through a mask[.];

[3] ~~a step of~~ removing said exposed area by development to form a positive image[.];
and then

[4] ~~a step of~~ exposing a whole area of the positive image to light.

4. (currently amended) The [[A]] pattern forming method according to ~~any one of claims claim 1 to 3~~, which is ~~characterized in that~~ further comprises step [5] [[a]] heat treatment (post-baking) which is carried out after the whole area exposure step ~~described before~~.

5. (currently amended) A pattern forming method according to ~~any one of claims claim 1 to 4~~, wherein ~~which is characterized in that said~~ (a) the alkali-soluble resin is at least one species selected from the group consisting of novolak resin, polyvinyl phenolic resins and acrylic resins.

6. (currently amended) A pattern forming method according to ~~any one of claims claim 1 to 5~~, which is ~~characterized in that~~ wherein the mask used ~~at in [2]~~ the exposure step ~~described before~~ is a mask having a half-tone region which is partially made 10 to 90 % of transmittance at a light transmission region being equipped with a semi-transparent film or installing a slit or a mesh having a dimension of not more than a resolution of the exposure device.

7. (new) The pattern forming method according to claim 2, which further comprises step [5] heat treatment (post-baking) which is carried out after the whole area exposure step.

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8. (new) The pattern forming method according to claim 3, which further comprises step [5] heat treatment (post-baking) which is carried out after the whole area exposure step.
9. (new) A pattern forming method according to claim 2, wherein (a) the alkali-soluble resin is at least one species selected from the group consisting of novolak resin, polyvinyl phenolic resins and acrylic resins.
10. (new) A pattern forming method according to claim 3, wherein (a) the alkali-soluble resin is at least one species selected from the group consisting of novolak resin, polyvinyl phenolic resins and acrylic resins.
11. (new) A pattern forming method according to claim 4, wherein (a) the alkali-soluble resin is at least one species selected from the group consisting of novolak resin, polyvinyl phenolic resins and acrylic resins.
12. (new) A pattern forming method according to claim 2, wherein the mask used in [2] the exposure step is a mask having a half-tone region which is partially made 10 to 90 % of transmittance at a light transmission region being equipped with a semi-transparent film or installing a slit or a mesh having a dimension of not more than a resolution of the exposure device.
13. (new) A pattern forming method according to claim 3, wherein the mask used in [2] the exposure step is a mask having a half-tone region which is partially made 10 to 90 % of transmittance at a light transmission region being equipped with a semi-transparent

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film or installing a slit or a mesh having a dimension of not more than a resolution of the exposure device.

14. (new) A pattern forming method according to claim 4, wherein the mask used in [2] the exposure step is a mask having a half-tone region which is partially made 10 to 90 % of transmittance at a light transmission region being equipped with a semi-transparent film or installing a slit or a mesh having a dimension of not more than a resolution of the exposure device.

15. (new) A pattern forming method according to claim 5, wherein the mask used in [2] the exposure step is a mask having a half-tone region which is partially made 10 to 90 % of transmittance at a light transmission region being equipped with a semi-transparent film or installing a slit or a mesh having a dimension of not more than a resolution of the exposure device.